

Time	Coherence	Qubit	Material	Host	Date	Reference	Source	
57 s	T_1	LD/e	GaAs/AlGaAs	2D	2018-08	1	p3 and Fig. 4a	1
30 s	T_1	LD/i	Si:P	imp	2017-03	2	Fig. 2b the lowest point	2
10 s	T_1	LD/e	GaAs/AlGaAs	2D	2017-10	3	Fig. 2 the lowest green point	3
9.8 s	T_1	LD/i	Si:P	imp	2019-05	4	Fig. 2c	4
9.3 s	T_1	LD/i	Si:P	imp	2018-03	5	p3 and Fig. 1f	5
9 s	T_1	LD/e	Si/SiO ₂	1D	2021-03	6	p3 and Fig. 3a the leftmost blue point	6
6 s	T_1	LD/i	Si:P	imp	2010-09	7	p2	7
5 s ^a	T_1	LD/e	Si/SiGe	2D	2019-04	8	p4	8
4.2 s	T_1	LD/i	Si:P	imp	2019-01	9	p3	9
3.4 s	T_1	LD/i	²⁸ Si:P	imp	2021-01	10	p6 and SFig. 3c	10
3 s	T_1	LD/i	²⁸ Si:P	imp	2016-10	11	p3	11
3 s	T_1	ST/e	Si/SiGe	2D	2012-01	12	p4	12
2.8 s	T_1	LD/e	Si/SiGe	2D	2011-04	13	p3 and Fig. 3	13
2.6 s	T_1	LD/e	Si/SiO ₂	2D	2013-06	14	p3	14
1.8 s	T_1	LD/i	Si:P	imp	2013-06	15	Fig. 3	15
1.6 s	T_1	LD/e	²⁸ Si/SiO ₂	2D	2022-03	16	p4 and Fig. 3c	16
1.3 s	T_1	LD/i ^b	²⁸ Si:P	imp	2016-10	17	p4	17
1.3 s	T_1	LD/i	Si:P	imp	2018-11	18	p3 and Fig. 2b	18
1 s	T_1	LD/e	GaAs/AlGaAs	2D	2008-01	19	p4 and Fig. 3c the leftmost blue point	19
1 s	T_1	LD/e	²⁸ Si/SiO ₂	2D	2018-10	20	p2	20
1 s	T_1	LD/e	²⁸ Si/SiGe	2D	2020-03	21	p6 and Fig. 4a	21
0.7 s	T_1	LD/i	Si:P	imp	2012-09	22	p3	22
0.6 s ^c	T_1	LD/e	Si/SiGe	2D	2009-08	23	Fig. 5	23
0.5 s ^d	T_1	ST/e	²⁸ Si/SiO ₂	2D	2020-04	24	Fig. 4 the leftmost black point	24
0.17 s	T_1	LD/e	Si/SiGe	2D	2016-11	25	Fig. 6	25
0.16 s ^e	T_1	LD/e	Si/SiGe	2D	2019-04	8	Fig. 2	26
0.15 s ^f	T_1	LD/e	²⁸ Si/SiO ₂	2D	2018-08	26	p2 and p4	27
0.14 s	T_1	ST/e	Si/SiGe	2D	2012-04	27	Fig. 2d	28
0.13 s	T_1	LD/e	²⁸ Si/SiGe	2D	2019-11	28	p4	29
90 ms	T_1	LD/e	Si/SiO ₂	2D	2020-06	29	Fig. 1c	30
85 ms	T_1	LD/e	GaAs/AlGaAs	2D	2014-12	30	p2 and Fig. 3	31
50 ms	T_1	LD/e	Si/SiGe	2D	2018-02	31	p1 and ED Fig. 3b	32
40 ms	T_1	LD/e	Si/SiO ₂	2D	2010-03	32	p4 and Fig. 4 the leftmost red point	33
32 ms	T_1	LD/h	Ge/SiGe	2D	2020-08	33	p3	34
32 ms	T_1	LD/e	²⁸ Si/SiGe	2D	2022-04	34	p3	35
22 ms ^g	T_1	LD/e	Si/SiGe	2D	2022-08	35	p2 and ED Fig. 4b-d	36
20 ms	T_1	HY/e ^h	²⁸ Si/SiGe	2D	2021-12	36	p4	37
16 ms	T_1	LD/h	Ge/SiGe	2D	2021-03	37	Fig. S5 dot 3	38
15 ms ⁱ	T_1	ST/e	²⁸ Si/SiO ₂	2D	2020-04	24	Fig. 4 the rightmost black point	39
10 ms	T_1	LD/e	Si/SiO ₂	1D	2021-09	38	p2 and Fig. 2a	40
8.4 ms	T_1	LD/h	BLG	2D	2022-05	39	p5 and Fig. 4	41
5 ms	T_1	LD/i	²⁸ Si:B	imp	2020-07	40	p3 and Fig. 3b	42
5 ms ^j	T_1	ST/e	²⁸ Si/SiO ₂	2D	2021-01	41	p4 and Fig. 1d	43
4.1 ms	T_1	ST/i	Si:P	imp	2014-06	42		44
3.7 ms	T_1	LD/e	GaAs/AlGaAs	2D	2016-07	43	p3 and Fig. 2	45
3.7 ms	T_1	LD/e ^k	²⁸ Si/SiO ₂	2D	2020-04	44	p2	46
3.1 ms	T_1	LD/i	²⁸ Si:P	imp	2022-01	45	ED Fig. 3 first column	47
2.8 ms ^l	T_1	LD/e	²⁸ Si/SiO ₂	2D	2018-08	26	p4 and Fig. 3a	48
2.3 ms ^m	T_1	ST/e	GaAs/AlGaAs	2D	2007-03	46	p2	49
1.5 ms	T_1	LD/e	GaAs/AlGaAs	2D	2019-04	47	Fig. 2	50

TABLE I-1. Spin coherence times (part 1). Superscripts stand for the following. ^a: No micromagnet. ^b: Qubit defined in the rotating frame. ^c: (*estimated*) Fig. 5 the lowest point. ^d: At 0.04 kelvin. ^e: With micromagnet. ^f: At 0.1 kelvin. ^g: The average over the three qubits. ^h: EO qubit. ⁱ: At 1.5 kelvin. ^j: Lifetime of T_- state. ^k: At 1 kelvin. ^l: At 1.1 kelvin. ^m: Triplet-singlet relaxation in a single dot.

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